



STS3DPFS30L

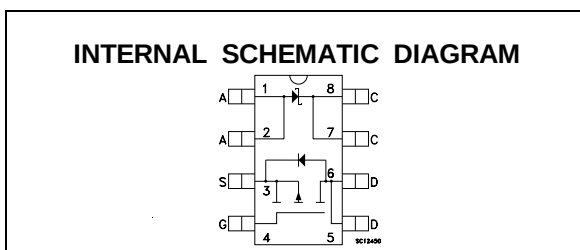
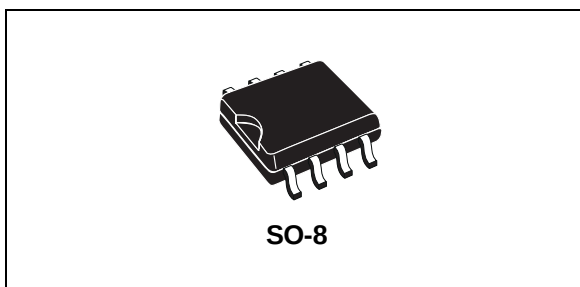
STripFET™ P - CHANNEL 30V - 0.13Ω - 3A S0-8 MOSFET PLUS SCHOTTKY RECTIFIER

PRELIMINARY DATA

MAIN PRODUCT CHARACTERISTICS			
MOSFET	V _{DSS}	R _{DS(on)}	I _D
	30V	<0.16Ω	3A
SCHOTTKY	I _{F(AV)}	V _{RRM}	V _{F(MAX)}
	3A	30V	0.51V

DESCRIPTION:

This product associates the latest low voltage StripFET™ in p-channel version to a low drop Schottky diode. Such configuration is extremely versatile in implementing, a large variety of DC-DC converters for printers, portable equipment, and cellular phones.



MOSFET ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	3	A
I _D	Drain Current (continuous) at T _c = 100 °C	1.9	A
I _{DM} (•)	Drain Current (pulsed)	12	A
P _{tot}	Total Dissipation at T _c = 25 °C	2	W

SCHOTTKY ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage		30	V
I _{F(RMS)}	RMS Forward Current		20	A
I _{F(AV)}	Average Forward Current	T _L =125 °C δ=0.5	3	A
I _{FSM}	Surge Non Repetitive Forward Current	tp= 10 ms Sinusoidal	75	A
I _{RSM}	Non Repetitive Peak Reverse Current	tp=100 μs	1	A
dv/dt	Critical Rate Of Rise Of Reverse Voltage		10000	V/μs

(•) Pulse width limited by safe operating area

Note: For the P-CHANNEL MOSFET actual polarity of voltages and current has to be reversed

THERMAL DATA

R _{thj-amb}	(*)Thermal Resistance Junction-ambient MOSFET S.O. Dual Operating	78	°C/W
R _{thj-amb}	(*) Thermal Resistance Junction-ambientSCHOTTKY	62	°C/W
T _{stg}	Storage Temperature Range	100	°C/W
T _j	Junction Temperature	-65 to 150	°C
	(*) mounted on FR-4 board (steady state)	150	°C

MOSFET ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16 V			± 1	µA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	1		2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 1.5 A V _{GS} = 4.5V I _D = 1.5 A		0.13 0.15	0.16 0.19	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	3			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 1.5 A		3.5		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		510		pF
C _{oss}	Output Capacitance			170		pF
C _{rss}	Reverse Transfer Capacitance			55		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}$ $I_D = 1.5\text{ A}$		15		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, see fig. 3)		37		ns
Q_g	Total Gate Charge	$V_{DD} = 15\text{ V}$ $I_D = 3\text{ A}$ $V_{GS} = 4.5\text{ V}$		5.5	7.5	nC
Q_{gs}	Gate-Source Charge			1.7		nC
Q_{gd}	Gate-Drain Charge			1.8		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 15\text{ V}$ $I_D = 1.5\text{ A}$		15		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, see fig. 3)		29		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				3	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				12	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 3\text{ A}$ $V_{GS} = 0$			2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 3\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 15\text{ V}$ $T_J = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		18		ns
Q_{rr}	Reverse Recovery Charge			12		nC
I_{RRM}	Reverse Recovery Current			1.33		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

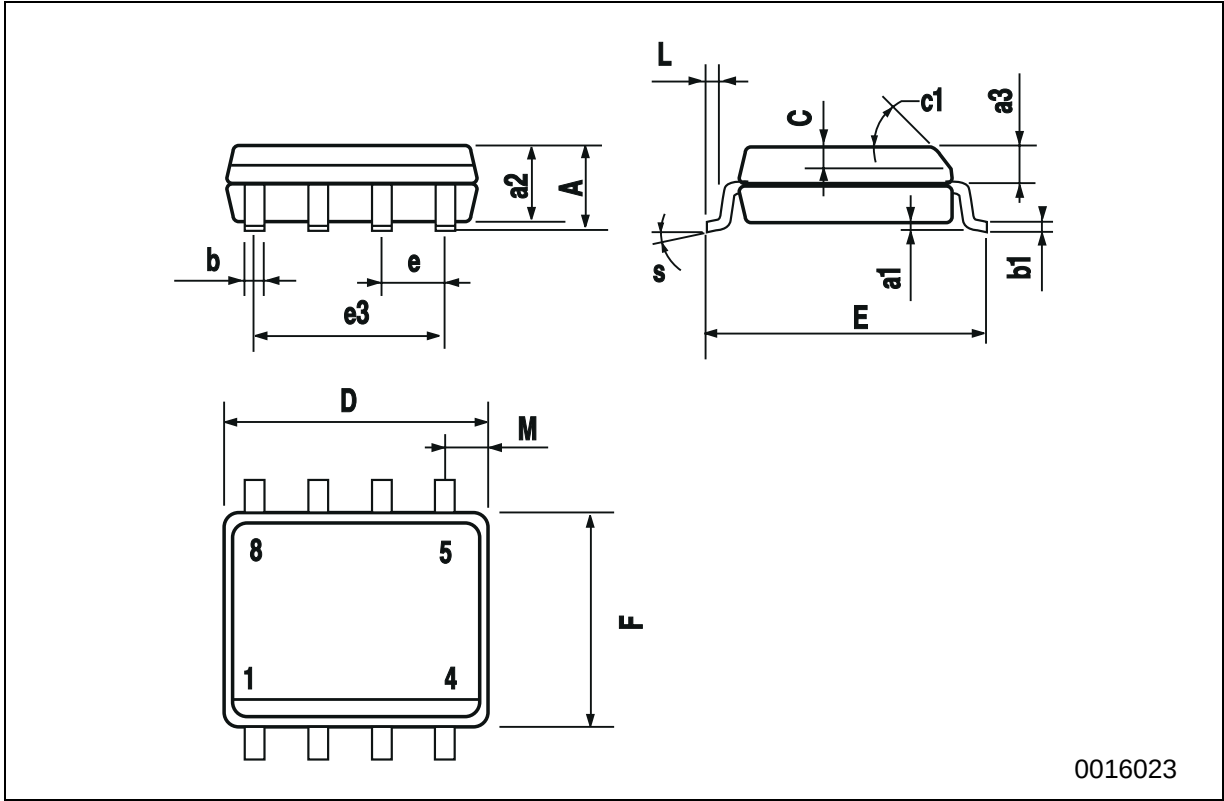
($\bullet$) Pulse width limited by safe operating area

SCHOTTKY STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_R(*)$	Reversed Leakage Current	$T_J = 25\text{ }^\circ\text{C}$ $V_R = 30\text{ V}$ $T_J = 125\text{ }^\circ\text{C}$ $V_R = 30\text{ V}$		0.03	0.2 100	mA mA
$V_F(*)$	Forward Voltage drop	$T_J = 25\text{ }^\circ\text{C}$ $I_F = 3\text{ A}$ $T_J = 125\text{ }^\circ\text{C}$ $I_F = 3\text{ A}$		0.38	0.51 0.46	V V

SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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